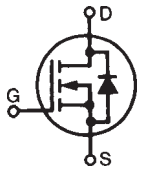
IXYS

Linear™ Power MOSFET w/ Extended FBSOA

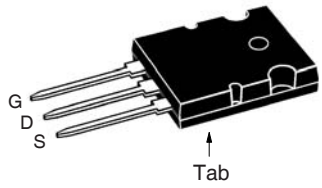
IXTK17N120L
IXTX17N120L

V_{DSS} = 1200V
I_{D25} = 17A
$R_{DS(on)}$ ≤ 900mΩ

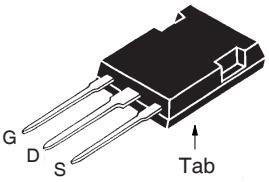
N-Channel Enhancement Mode
Avalanche Rated
Guaranteed FBSOA



TO-264 (IXTK)



PLUS247 (IXTX)



G = Gate D = Drain
S = Source Tab = Drain

Symbol	Test Conditions	Maximum Ratings	
V_{DSS}	T_J = 25°C to 150°C	1200	V
V_{DGR}	T_J = 25°C to 150°C, R_{GS} = 1MΩ	1200	V
V_{GSS}	Continuous	±30	V
V_{GSM}	Transient	±40	V
I_{D25}	T_C = 25°C	17	A
I_{DM}	T_C = 25°C, pulse width limited by T_{JM}	34	A
I_A	T_C = 25°C	8.5	A
E_{AS}	T_C = 25°C	2.5	J
P_D	T_C = 25°C	700	W
T_J		-55...+150	°C
T_{JM}		150	°C
T_{stg}		-55...+150	°C
T_L	1.6mm (0.063 in.) from case for 10s	300	°C
T_{SOLD}	Plastic body for 10s	260	°C
M_d	Mounting torque (IXTK)	1.13/10	Nm/lb.in.
F_C	Mounting Force (IXTX)	20..120 / 4.5..27	N/lb.
Weight	TO-264	10	g
	PLUS247	6	g

Symbol	Test Conditions (T_J = 25°C, Unless Otherwise Specified)	Characteristic Values Min.	Typ.	Max.	
BV_{DSS}	V_{GS} = 0V, I_D = 1mA	1200			V
$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = 250μA	3.0		6.0	V
I_{GSS}	V_{GS} = ±30V, V_{DS} = 0V			±200	nA
I_{DSS}	V_{DS} = V_{DSS}, V_{GS} = 0V			50	μA
	T_J = 125°C			2	mA
$R_{DS(on)}$	V_{GS} = 20V, I_D = 0.5 • I_{DSS}, Note 1			900	mΩ

Features

- Designed for Linear Operations
- Guaranteed FBSOA at 60ºC
- Avalanche Rated
- Low $R_{DS(on)}$ HDMOS™ Process
- Molding Epoxies Meet UL94 V-0 Flammability Classification

Advantages

- Easy to Mount
- Space Savings
- High Power Density

Applications

- Programmable Loads
- Current Regulators
- DC-DC Convertors
- Battery Chargers
- DC Choppers
- Temperature and Lighting Controls

Symbol	Test Conditions (T_J = 25°C, Unless Otherwise Specified)	Characteristic Values Min.	Typ.	Max.	
g_{fs}	V_{DS} = 20V, I_D = 0.5 • I_{DSS}, Note 1	3.5	5.0	6.5	S
C_{iss}	V_{GS} = 0V, V_{DS} = 25V, f = 1MHz		8300		pF
C_{oss}			520		pF
C_{rss}			90		pF
$t_{d(on)}$	**Resistive Switching Times**		42		ns
t_r	V_{GS} = 15V, V_{DS} = 0.5 • V_{DSS}, I_D = 0.5 • I_{DSS}		31		ns
$t_{d(off)}$	R_G = 2Ω (External)		110		ns
t_f			83		ns
$Q_{g(on)}$	V_{GS} = 15V, V_{DS} = 0.5 • V_{DSS}, I_D = 0.5 • I_{DSS}		155		nC
Q_{gs}			41		nC
Q_{gd}			60		nC
R_{thJC}				0.18	°C/W
R_{thCS}			0.15		°C/W

Safe Operating Area Specification

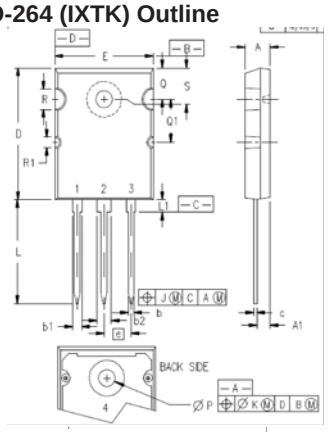
Symbol	Test Conditions	Characteristic Values Min.	Typ.	Max.	
SOA	V_{DS} = 800V, I_D = 0.3A, T_C = 60°C, t_P = 3s	240			W

Source-Drain Diode

Symbol	Test Conditions (T_J = 25°C, Unless Otherwise Specified)	Characteristic Values Min.	Typ.	Max.	
I_S	V_{GS} = 0V			17	A
I_{SM}	Repetitive, Pulse Width Limited by T_{JM}			50	A
V_{SD}	I_F = 17A, V_{GS} = 0V, Note 1			1.5	V
t_{rr}	I_F = I_S, -di/dt = 100A/μs, V_R = 100V		1830		ns

Note: 1. Pulse test, t ≤ 300μs, duty cycle, d ≤ 2%.

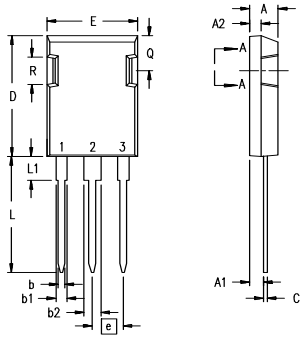
TO-264 (IXTK) Outline



1 – GATE
2, 4 – DRAIN (COLLECTOR)
3 – SOURCE (EMITTER)

SYM	INCHES MIN	INCHES MAX	MILLIMETERS MIN	MILLIMETERS MAX
A	.185	.209	4.70	5.31
A1	.102	.118	2.59	3.00
b	.037	.055	0.94	1.40
b1	.087	.102	2.21	2.59
b2	.110	.126	2.79	3.20
c	.017	.029	0.43	0.74
D	1.007	1.047	25.58	26.59
E	.760	.799	19.30	20.29
e	.215BSC		5.46 BSC	
J	.000	.010	0.00	0.25
K	.000	.010	0.00	0.25
L	.779	.842	19.79	21.39
L1	.087	.102	2.21	2.59
ØP	.122	.138	3.10	3.51
Q	.240	.256	6.10	6.50
Q1	.330	.346	8.38	8.79
ØR	.155	.187	3.94	4.75
ØR1	.085	.093	2.16	2.36
S	.243	.253	6.17	6.43

PLUS 247™ (IXTX) Outline



Terminals: 1 - Gate
2 - Drain (Collector)
3 - Source (Emitter)
4 - Drain (Collector)

Dim.	Millimeter Min.	Millimeter Max.	Inches Min.	Inches Max.
A	4.83	5.21	.190	.205
A_1	2.29	2.54	.090	.100
A_2	1.91	2.16	.075	.085
b	1.14	1.40	.045	.055
b_1	1.91	2.13	.075	.084
b_2	2.92	3.12	.115	.123
C	0.61	0.80	.024	.031
D	20.80	21.34	.819	.840
E	15.75	16.13	.620	.635
e	5.45 BSC		.215 BSC	
L	19.81	20.32	.780	.800
L1	3.81	4.32	.150	.170
Q	5.59	6.20	.220	0.244
R	4.32	4.83	.170	.190

Fig. 1. Output Characteristics @ T_J = 25ºC

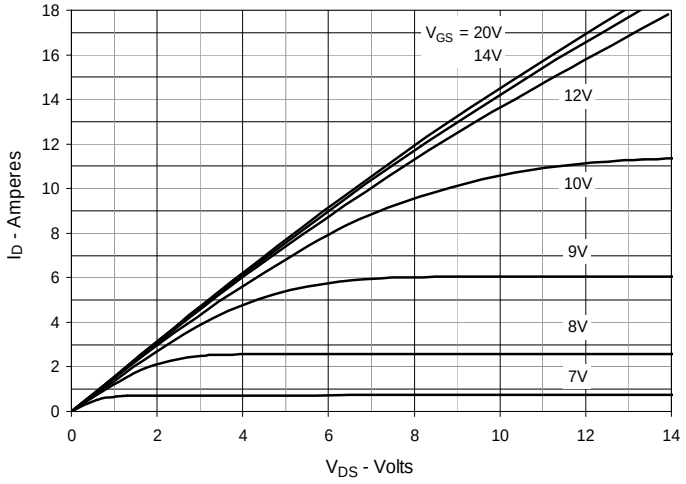


Fig. 2. Extended Output Characteristics @ T_J = 25ºC

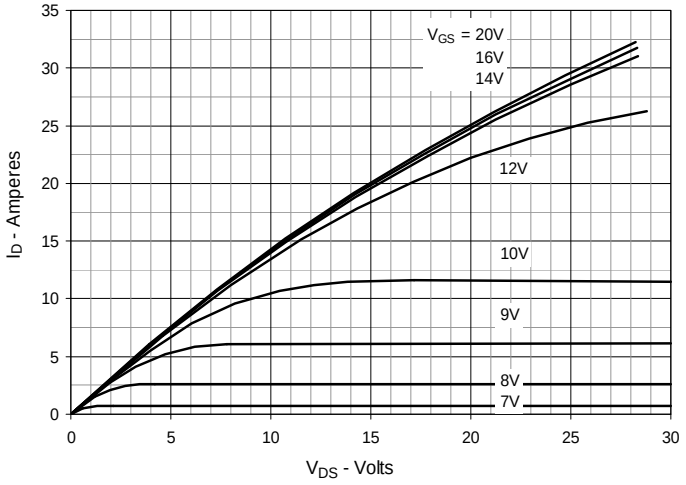


Fig. 3. Output Characteristics @ T_J = 125ºC

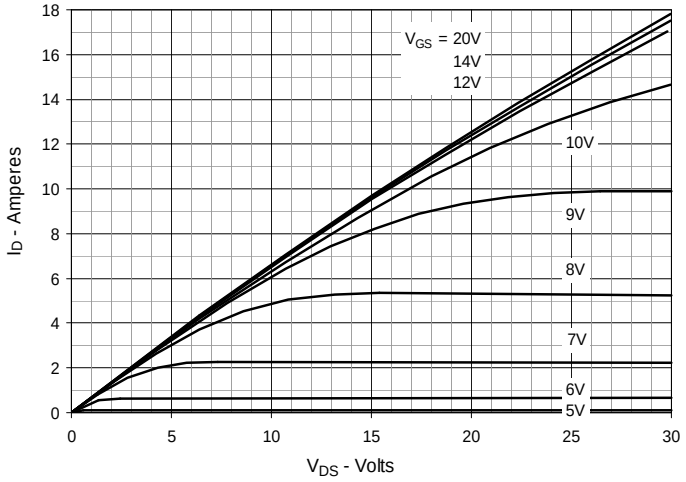


Fig. 4. $R_{DS(on)}$ Normalized to I_D = 8.5A Value vs. Junction Temperature

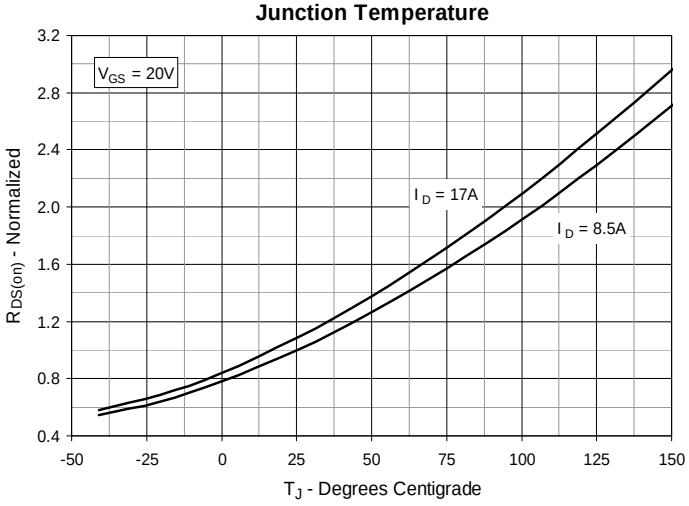


Fig. 5. $R_{DS(on)}$ Normalized to I_D = 8.5A Value vs. Drain Current

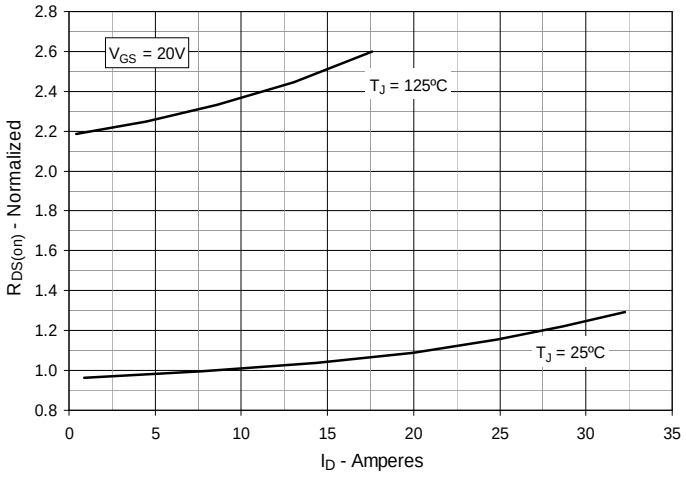


Fig. 6. Maximum Drain Current vs. Case Temperature

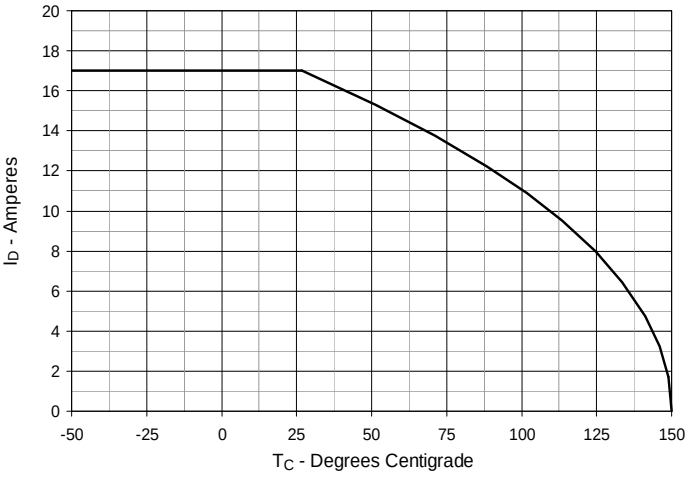


Fig. 7. Input Admittance

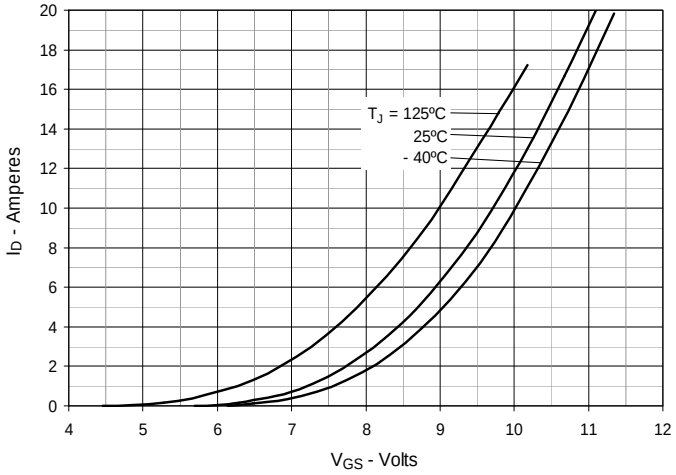


Fig. 8. Transconductance

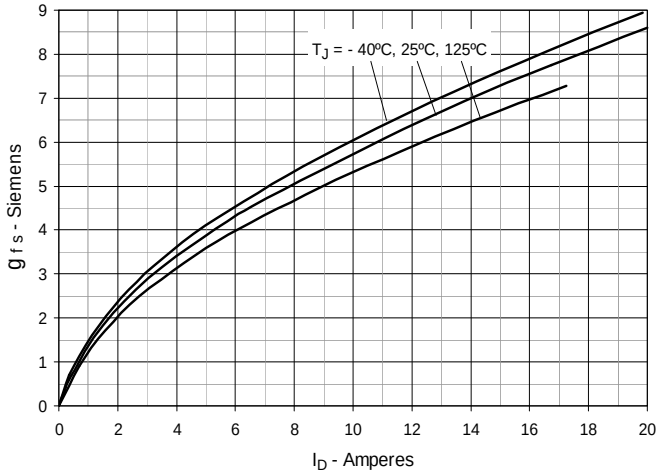


Fig. 9. Forward Voltage Drop of Intrinsic Diode

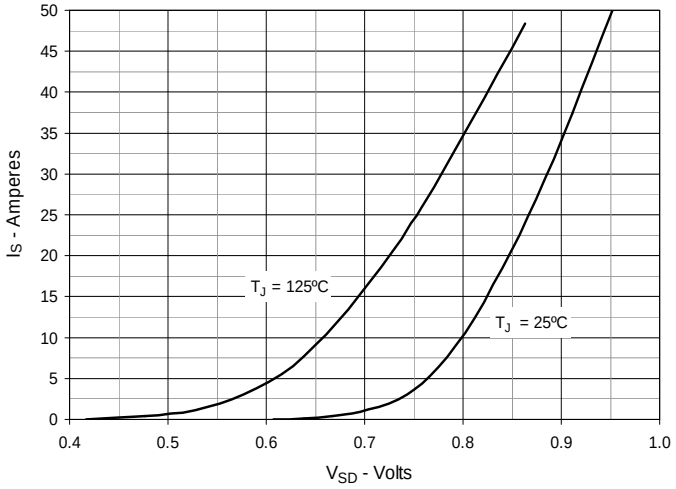


Fig. 10. Gate Charge

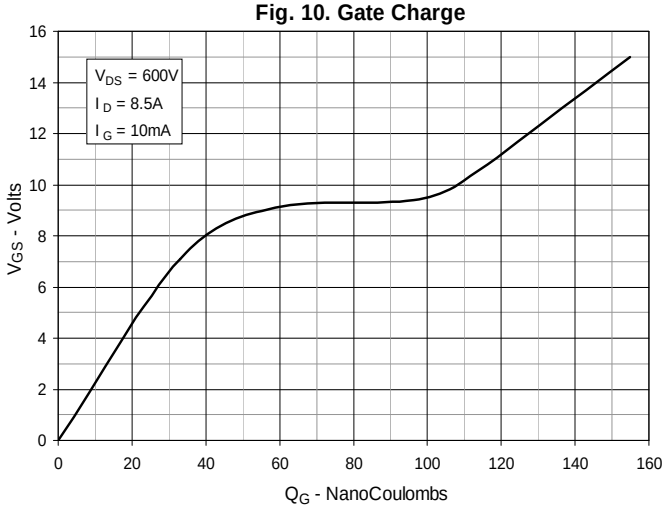


Fig. 11. Capacitance

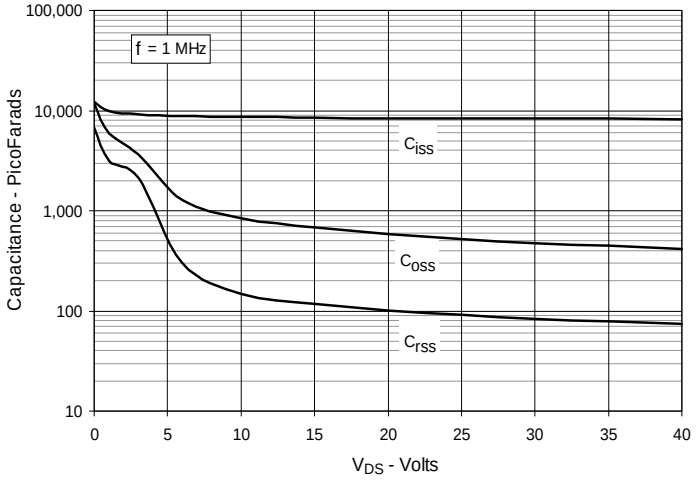


Fig. 12. Maximum Transient Thermal Impedance